

BC2303

P-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = -30V, I_D = -2.5A$
- $R_{DS(on)} < 78m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 105m\Omega @ V_{GS} = -4.5V$

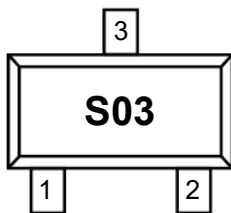
Features

- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 1

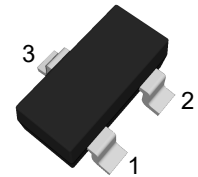
Application

- Load Switch
- PWM Application
- Power Management

Marking Code



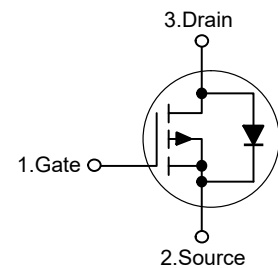
SOT-23



(Top View)

Pin	Description
1	Gate
2	Source
3	Drain

Schematic Diagram



Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	$-I_D$	2.5	A
Drain Current-Pulsed ^{Note1}	$-I_{DM}$	20	A
Maximum Power Dissipation	P_D	0.9	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	139	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

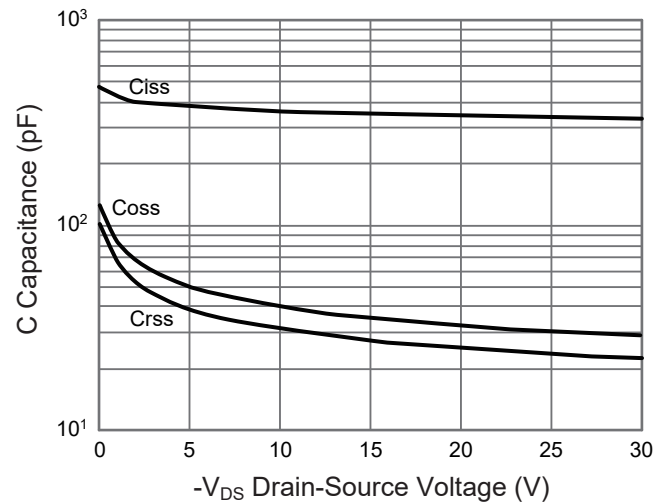
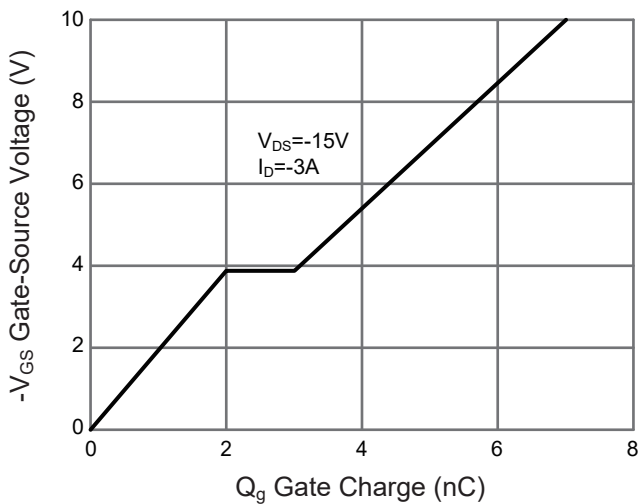
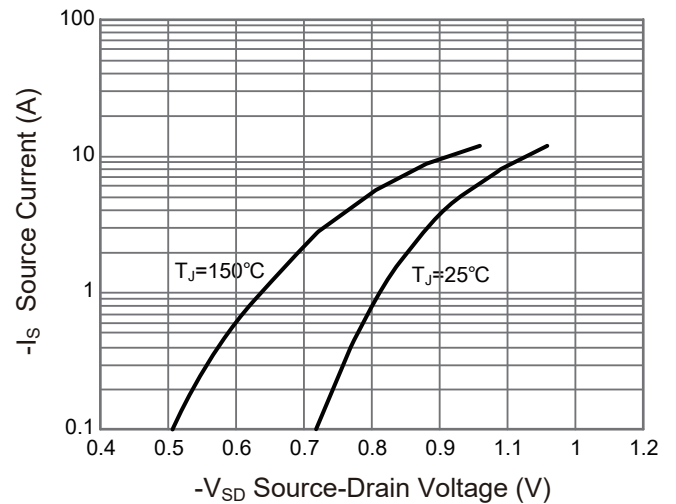
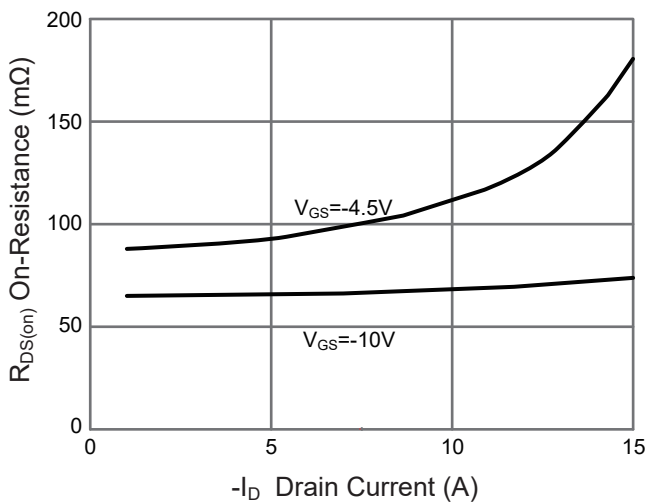
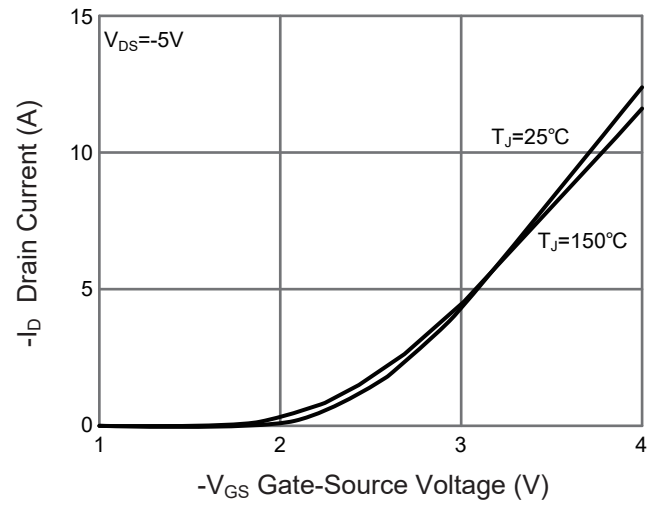
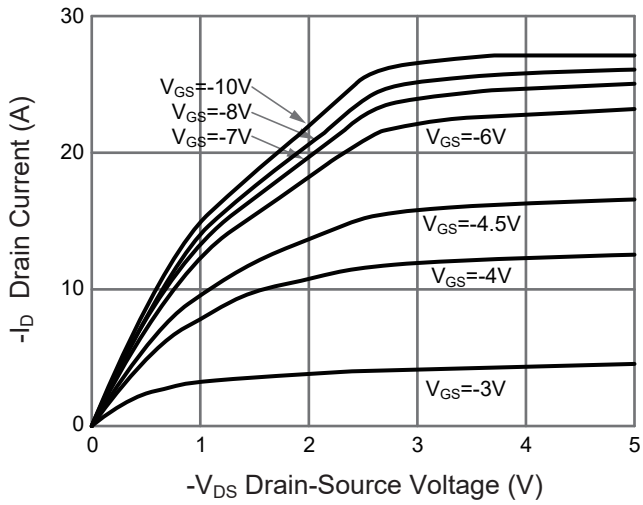
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	$-I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note3}	$-V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-2A$	--	66	78	m Ω
		$V_{GS}=-4.5V, I_D=-1.5A$	--	89	105	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=-5V, I_D=-1A$	--	3.9	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$	--	372	--	pF
Output Capacitance	C_{oss}		--	50	--	pF
Reverse Transfer Capacitance	C_{rss}		--	41	--	pF
Gate Resistance	R_G	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	--	11	--	Ω
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-3A,$ $V_{GS}=-10V$	--	7	--	nC
Gate-Source Charge	Q_{gs}		--	2	--	nC
Gate-Drain Charge	Q_{gd}		--	1	--	nC
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-3A,$ $V_{GS}=-10V, R_{GEN}=3\Omega$	--	5	--	nS
Turn-on Rise Time	t_r		--	23	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	21	--	nS
Turn-off Fall Time	t_f		--	30	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	$-V_{SD}$	$V_{GS}=0V, I_S=-2.5A$	--	--	1.2	V
Diode Forward Current ^{Note2}	$-I_S$		--	--	2.5	A

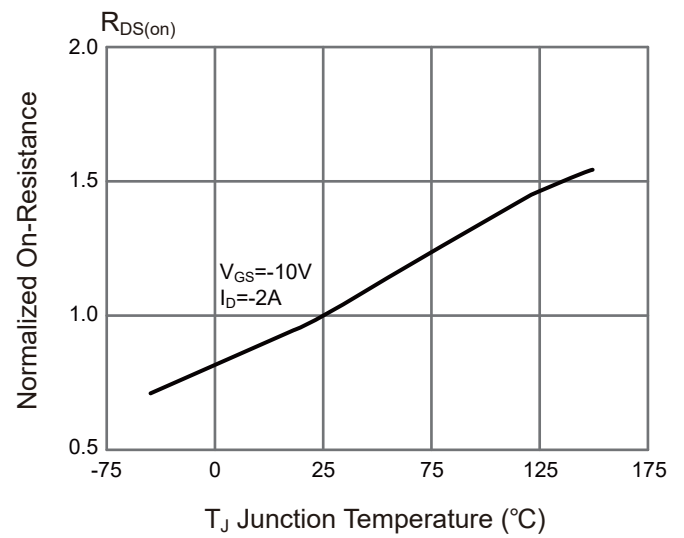
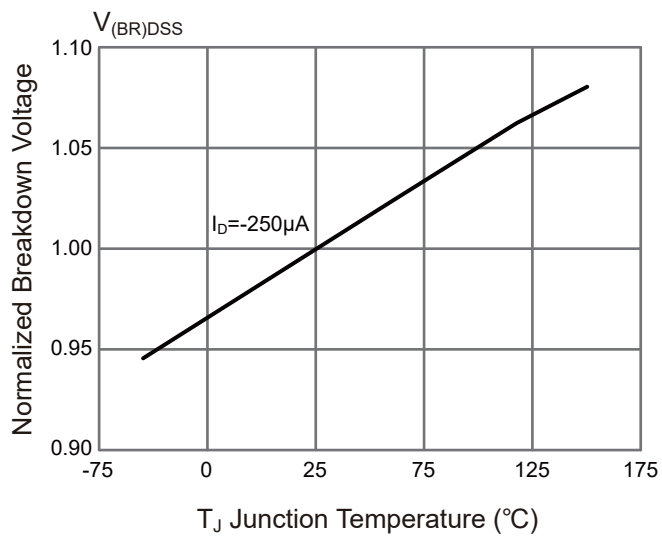
Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

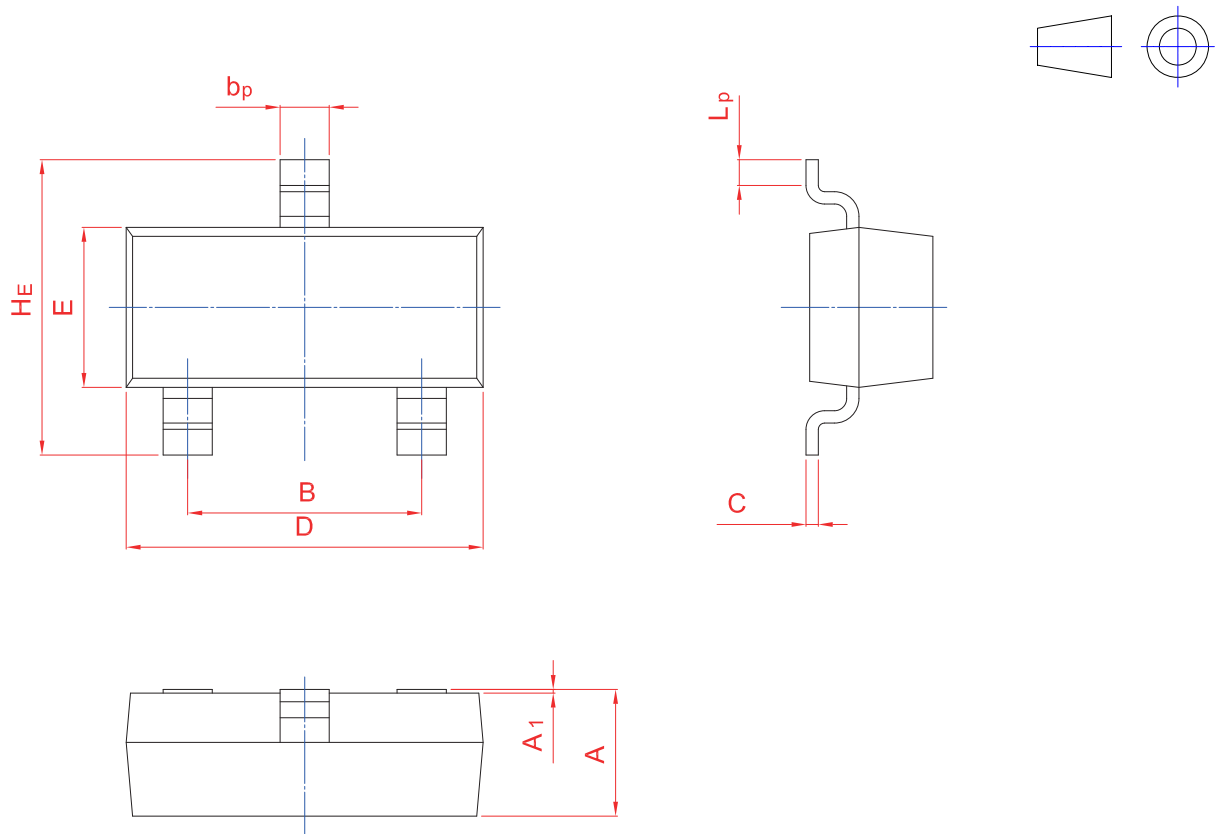
Typical Characteristic Curves





PACKAGE OUTLINE

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.89	2.04 1.78	0.51 0.30	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20